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## **PS3-15 Modelling the Deflection of 855 MeV Relativistic Electrons by a Bent Silicon Crystal Using TROPICS Software Package**

*Thursday, 9 October 2014 17:00 (1h 30m)*

Modeling the deflection of 855 MeV electrons in (111) the planar channels bent crystal silicon performed by numerically solving the kinetic Fokker-Planck equation in the phase space of the transverse coordinates and velocities. It is shown that the simulation results do not describe the experiment.

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